

Serial No.09/975,297
HP Docket No: 10007286-1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Date: June 26, 2003

Viatcheslav Ossipov et al.

Serial No.:09/975,297

Group Art Unit: 2822

Filed: October 12, 2001

Examiner: Soward, Ida M.

For: HIGH CURRENT AVALANCHE-TUNNELING AND INJECTION
TUNNELING SEMICONDUCTOR-DIELECTRIC-METAL STABLE
COLD EMITTER, WHICH EMULATES THE NEGATIVE ELECTRON
AFFINITY MECHANISM OF EMISSION

Honorable Commissioner of Patents and Trademarks
Alexandria, VA 22313-1450

FAX RECEIVED

JUN 26 2003

TECHNOLOGY CENTER 2800

RESPONSE TO OFFICE ACTION

Sir:

In response to the Office Action dated March 27, 2003, please enter the following
amendments and remarks into the above-identified application:

AMENDMENTS

Please amend the application in the following manner:

IN THE CLAIMS

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1. (Twice Amended) An electron emitter comprising:
a p region;
a dielectric layer formed directly above said p region;
a metallic layer formed directly above said dielectric layer; and
means for emitting electrons through said metallic layer.